

Radar Pulsed Power Transistor, 20W, 300 μ s Pulse, 10% Duty 3.1 - 3.4 GHz

PH3134-20L

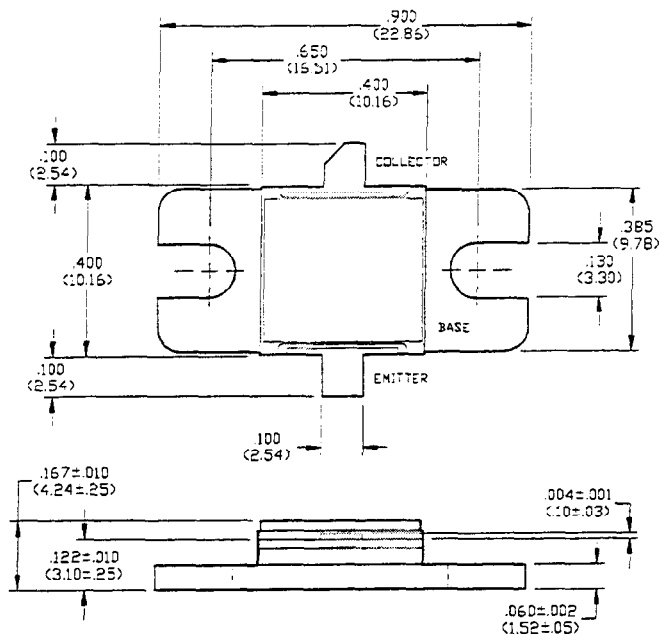
V2.00

Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EB0}	3.0	V
Collector Current (Peak)	I_C	2.4	A
Total Power Dissipation	P_{TOT}	146	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-65 to +200	°C



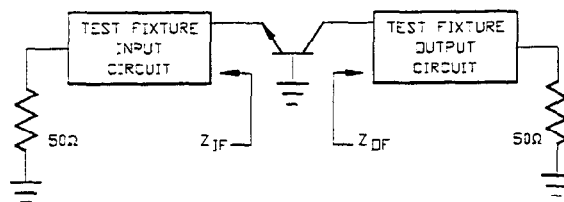
UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES $\pm .005$ "
(MILLIMETERS $\pm .13$ MM)

Electrical Characteristics at 25°C

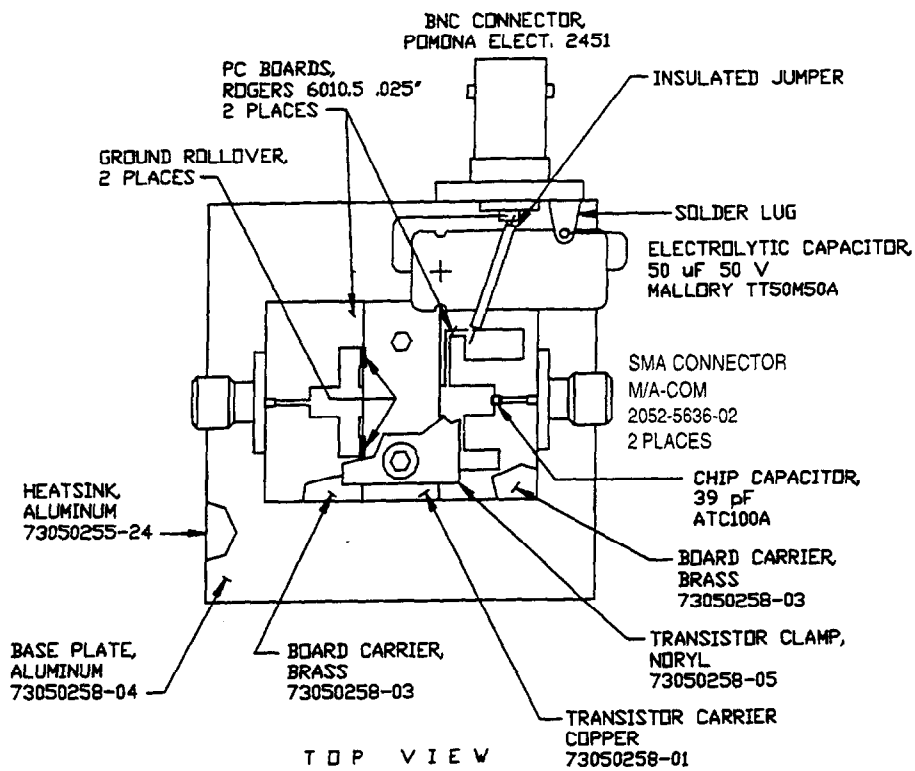
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	BV_{CES}	65	-	V	$I_C = 10$ mA
Collector-Emitter Leakage Current	I_{CES}	-	1.5	mA	$V_{CE} = 40$ V
Thermal Resistance	$R_{TH(JC)}$	-	1.2	°C/W	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.1, 3.25, 3.4$ GHz
Input Power	P_{IN}	-	3.56	W	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.1, 3.25, 3.4$ GHz
Power Gain	G_P	7.5	-	dB	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.1, 3.25, 3.4$ GHz
Collector Efficiency	η_C	35	-	%	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.1, 3.25, 3.4$ GHz
Input Return Loss	RL	6	-	dB	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.1, 3.25, 3.4$ GHz
Load Mismatch Tolerance	VSWR-T	-	2:1	-	$V_{CC} = 36$ V, $P_{OUT} = 20$ W, $F = 3.25$ GHz

Broadband Test Fixture Impedances

F(GHz)	$Z_{IF}(\Omega)$	$Z_{OF}(\Omega)$
3.10	$16.0 + j5.0$	$19.0 + j3.0$
3.25	$14.5 + j2.0$	$15.5 - j2.0$
3.40	$11.5 + j0.0$	$10.0 - j3.5$



RF Test Fixture



Test Fixture PC Board Dimensions

